

H5N2522FP-E0-E

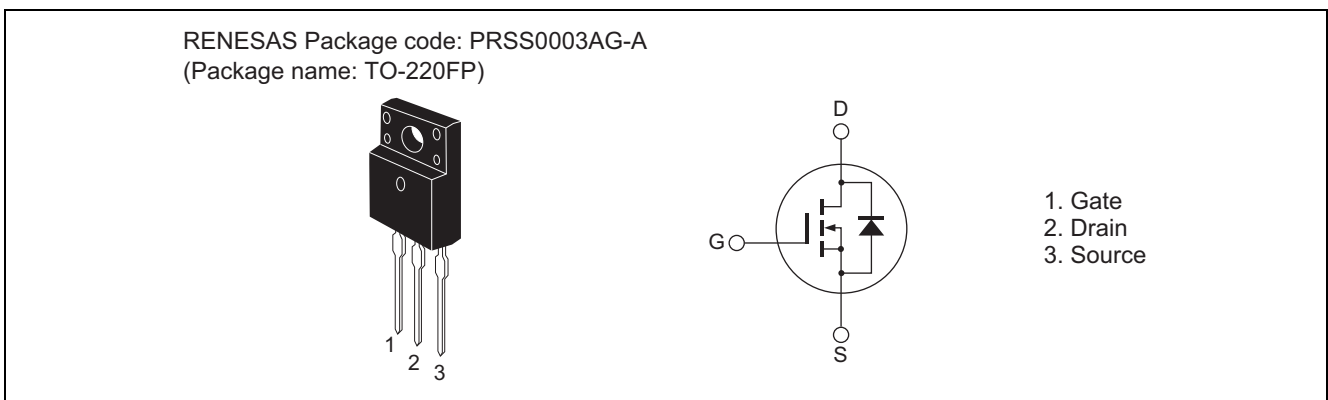
250V - 12A - MOS FET
High Speed Power Switching

R07DS0862EJ0100
Rev.1.00
Jul 27, 2012

Features

- Low on-resistance
 $R_{DS(on)} = 0.13 \Omega$ typ. (at $I_D = 6 \text{ A}$, $V_{GS} = 10 \text{ V}$, $T_a = 25^\circ\text{C}$)
- Low leakage current
- High speed switching
- Built-in fast recovery diode

Outline



Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

| Item | Symbol | Ratings | Unit |
|---|----------------------------------|-------------|---------------------------|
| Drain to Source voltage | V_{DSS} | 250 | V |
| Gate to source voltage | V_{GSS} | ± 30 | V |
| Drain current | I_D | 12 | A |
| Drain peak current | $I_{D(pulse)}$ ^{Note1} | 48 | A |
| Body-Drain diode reverse Drain current | I_{DR} | 12 | A |
| Body-Drain diode reverse Drain peak current | $I_{DR(pulse)}$ ^{Note1} | 48 | A |
| Avalanche current | I_{AP} ^{Note3} | 12 | A |
| Avalanche energy | E_{AR} ^{Note3} | 9 | mJ |
| Channel dissipation | P_{ch} ^{Note2} | 35 | W |
| Channel to case thermal impedance | θ_{ch-c} | 3.57 | $^\circ\text{C}/\text{W}$ |
| Channel temperature | T_{ch} | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Notes: 1. $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$
 2. Value at $T_c = 25^\circ\text{C}$
 3. $ST_{ch} = 25^\circ\text{C}$, $T_{ch} \leq 150^\circ\text{C}$

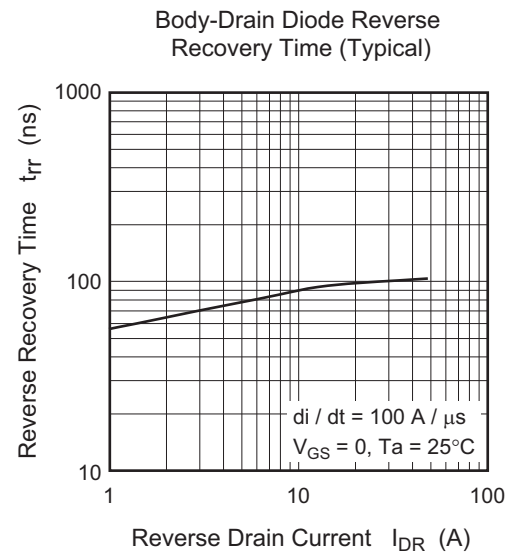
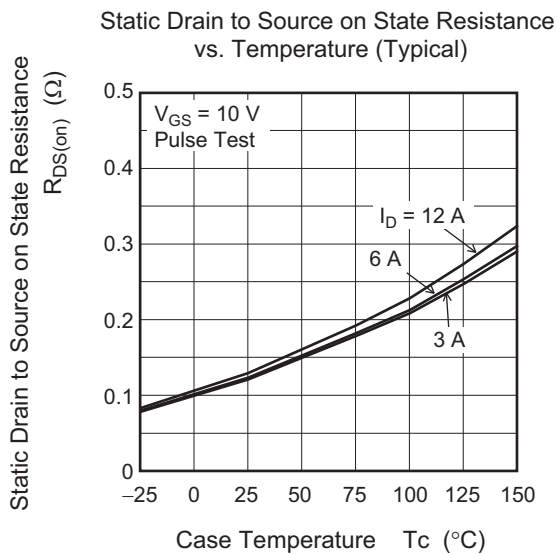
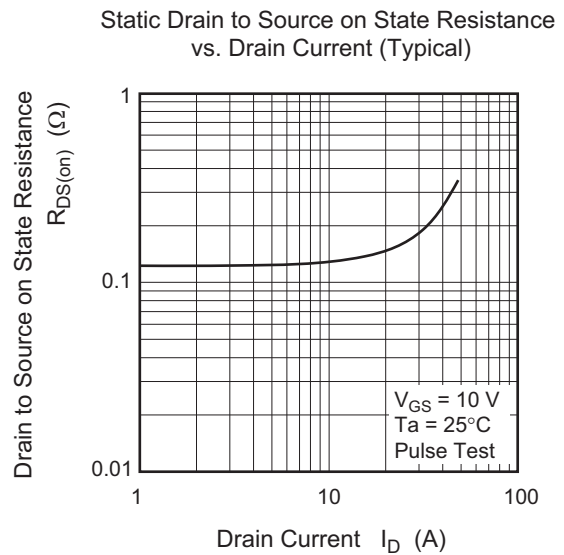
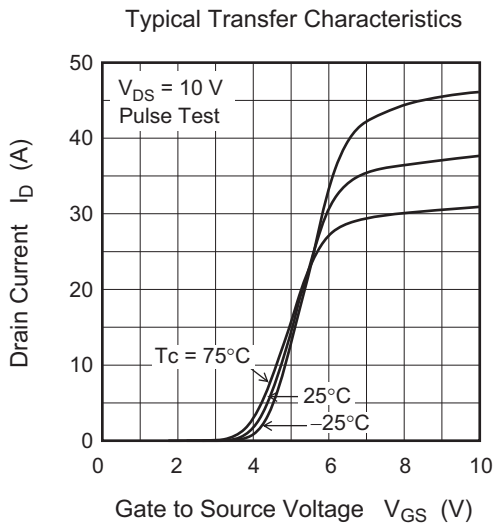
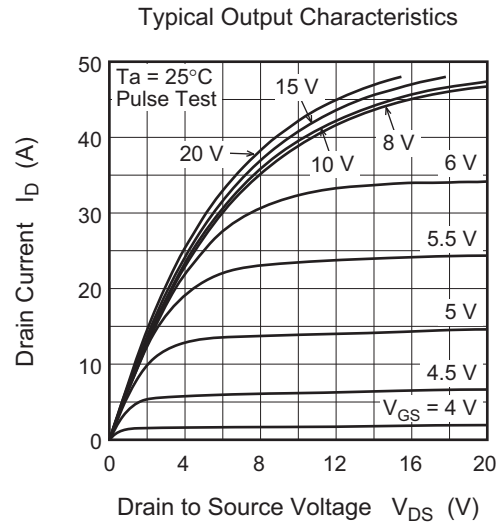
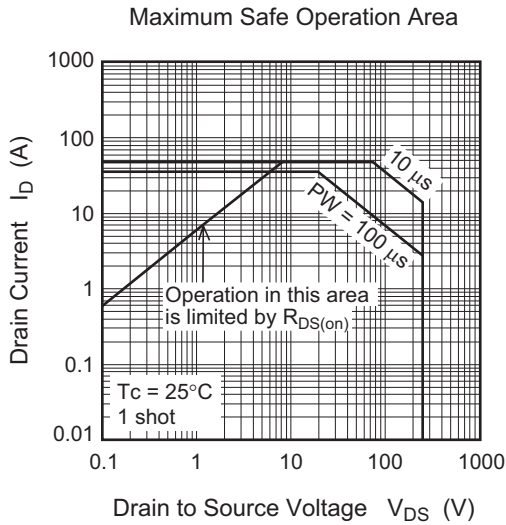
Electrical Characteristics

(Ta = 25°C)

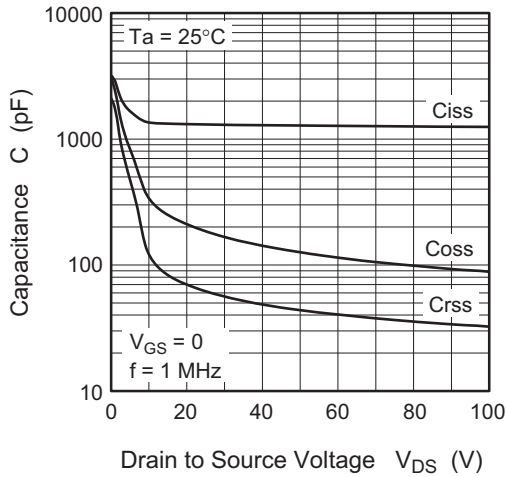
| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|--|---------------|-----|------|-----------|---------------|--|
| Drain to Source breakdown voltage | $V_{(BR)DSS}$ | 250 | — | — | V | $I_D = 10 \text{ mA}$, $V_{GS} = 0$ |
| Zero Gate voltage drain current | I_{DSS} | — | — | 10 | μA | $V_{DS} = 250 \text{ V}$, $V_{GS} = 0$ |
| Gate to Source leak current | I_{GSS} | — | — | ± 0.1 | μA | $V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0$ |
| Gate to Source cutoff voltage | $V_{GS(off)}$ | 1.5 | — | 4.0 | V | $V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$ |
| Static Drain to Source on state resistance | $R_{DS(on)}$ | — | 0.13 | 0.17 | Ω | $I_D = 6 \text{ A}$, $V_{GS} = 10 \text{ V}$ |
| Input capacitance | C_{iss} | — | 1300 | — | pF | $V_{DS} = 25 \text{ V}$ |
| Output capacitance | C_{oss} | — | 185 | — | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | C_{rss} | — | 62 | — | pF | $f = 1 \text{ MHz}$ |
| Turn-on delay time | $t_{d(on)}$ | — | 24 | — | ns | $I_D = 6 \text{ A}$ |
| Rise time | t_r | — | 57 | — | ns | $V_{GS} = 10 \text{ V}$ |
| Turn-off delay time | $t_{d(off)}$ | — | 190 | — | ns | $R_L = 20 \Omega$ |
| Fall time | t_f | — | 69 | — | ns | $R_g = 10 \Omega$ |
| Body-Drain diode forward voltage | V_{DF} | — | 0.89 | 1.35 | V | $I_F = 12 \text{ A}$, $V_{GS} = 0$ |
| Body-Drain diode reverse recovery time | t_{rr} | — | 93 | — | ns | $I_F = 12 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ |

Notes: 4. Pulse test

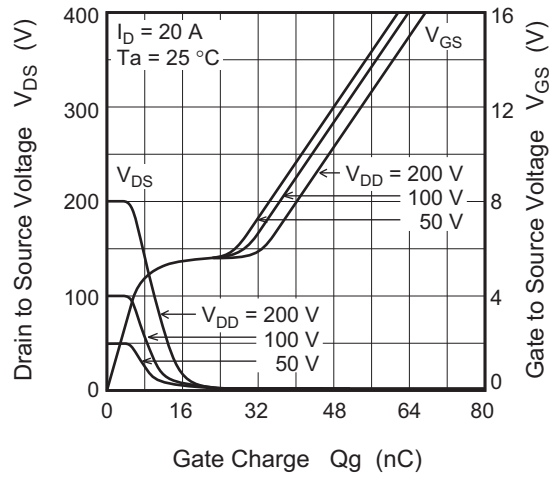
Main Characteristics



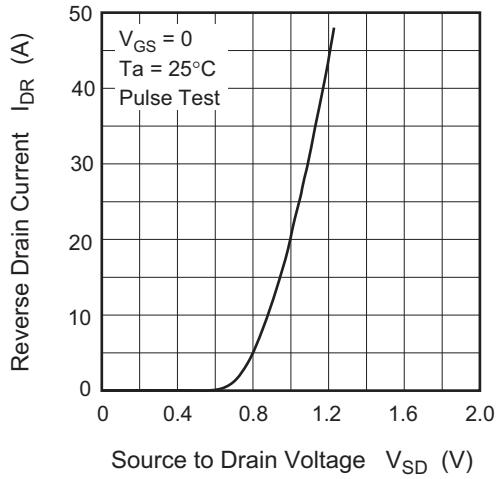
Typical Capacitance vs. Drain to Source Voltage



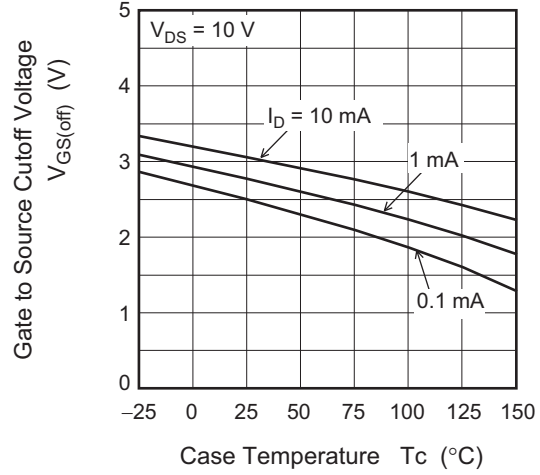
Dynamic Input Characteristics (Typical)



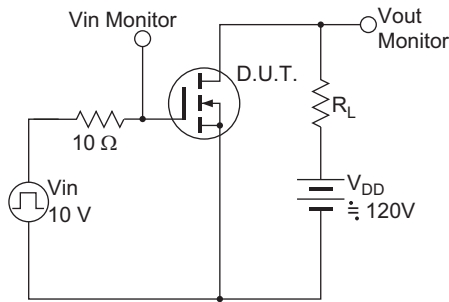
Reverse Drain Current vs. Source to Drain Voltage (Typical)



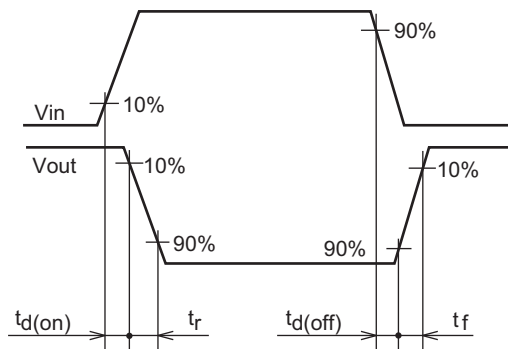
Gate to Source Cutoff Voltage vs. Case Temperature (Typical)



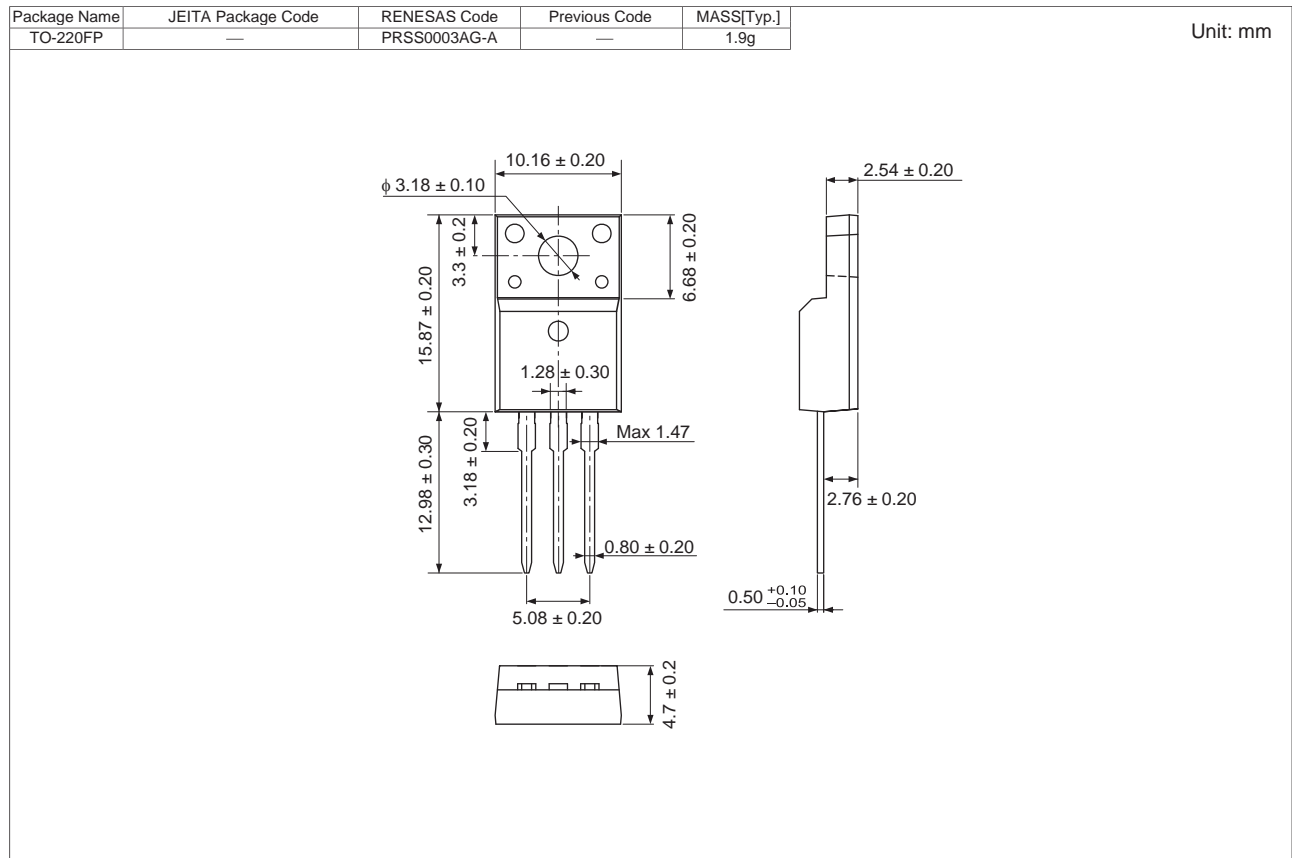
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| H5N2522FP-E0-E#T2 | 1000 pcs | Box (Tube) |

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Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
1 HarbourFront Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: +65-6213-0200, Fax: +65-6278-8001

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-3390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
11F., Samik Laved' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141